



150V 4.6mΩ TOLL N-Ch Power MOSFET

Features

- Ultra-low ON-resistance,  $R_{DS(ON)}$
- Low Gate Charge,  $Q_g$
- 100% UIS and  $R_g$  Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

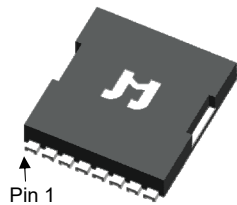
Product Summary

Parameter	Value	Unit
$V_{DS}$	150	V
$V_{GS(th\_Typ)}$	3.2	V
$I_D$ (@ $V_{GS} = 10V$ ) <sup>(2)</sup>	159	A
$R_{DS(ON)\_Typ}$ (@ $V_{GS} = 10V$ )	4.6	mΩ

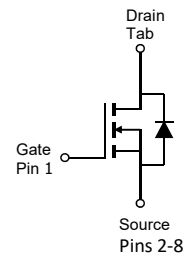
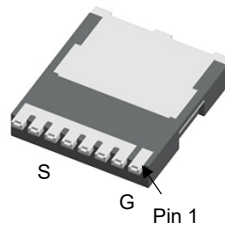
Applications

- Power Management in Computing, CE, IE 4.0, Communications
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- Load Switching, Quick/Wireless Charging, Motor Driving

PowerJE®10x12 Top



PowerJE®10x12 Bottom



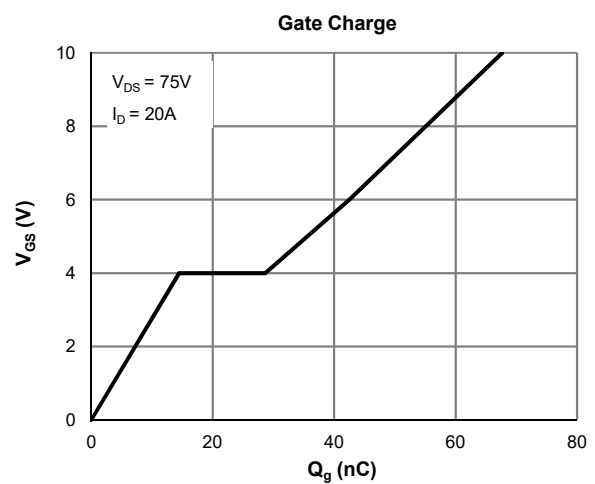
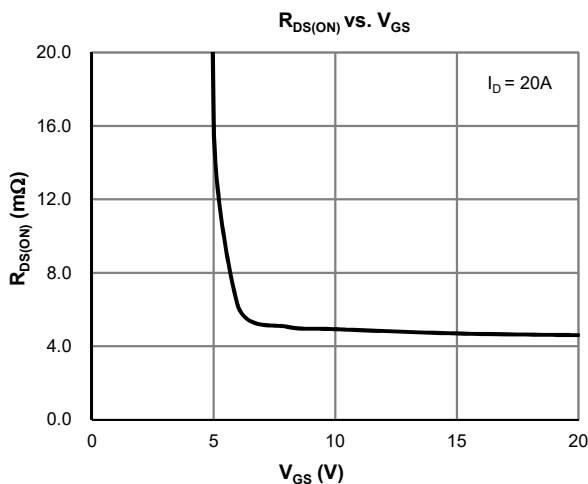
Ordering Information

Device	Package	# of Pins	Marking	MSL	$T_J$ (°C)	Media	Quantity (pcs)
JMSH1505ATL-13	PowerJE®10x12 <sup>(1)</sup>	8	SH1505A	1	-55 to 175	13-inch Reel	2000

Note 1: PowerJE® is a registered trademark of JieJie Micro., its package outline is compatible to that of TO-LeadLess (TOLL).

Absolute Maximum Ratings (@  $T_A = 25^\circ C$  unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	150	V
Gate-to-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current <sup>(2)</sup>	$I_D$	$T_C = 25^\circ C$	159
		$T_C = 100^\circ C$	113
Pulsed Drain Current <sup>(3)</sup>	$I_{DM}$	637	A
Avalanche Current <sup>(4)</sup>	$I_{AS}$	40	A
Avalanche Energy <sup>(4)</sup>	$E_{AS}$	800	mJ
Power Dissipation <sup>(5)</sup>	$P_D$	$T_C = 25^\circ C$	375
		$T_C = 100^\circ C$	188
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	°C



**Electrical Characteristics** (@  $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	150			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 120\text{V}, V_{GS} = 0\text{V}$			1.0	$\mu\text{A}$
					5.0	
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.5	3.2	4.5	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$		4.6	5.8	$\text{m}\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{V}, I_D = 20\text{A}$		97		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.67	1.0	V
Diode Continuous Current	$I_S$	$T_C = 25^\circ\text{C}$			375	A

**DYNAMIC PARAMETERS** <sup>(6)</sup>

Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 75\text{V}, f = 1\text{MHz}$		4320		pF
Output Capacitance	$C_{oss}$			535		pF
Reverse Transfer Capacitance	$C_{rss}$			7.2		pF
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.1		$\Omega$

**SWITCHING PARAMETERS** <sup>(6)</sup>

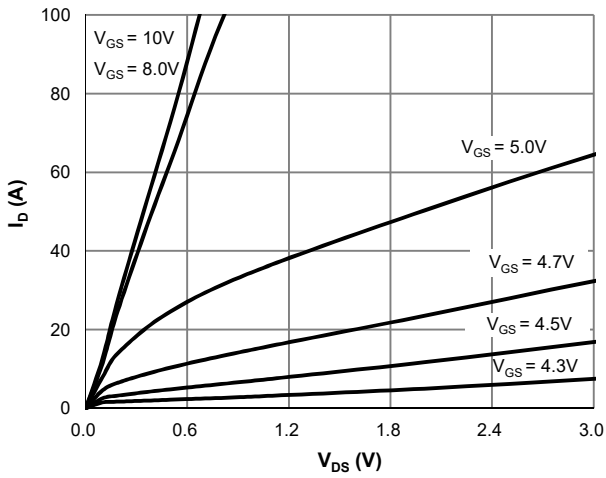
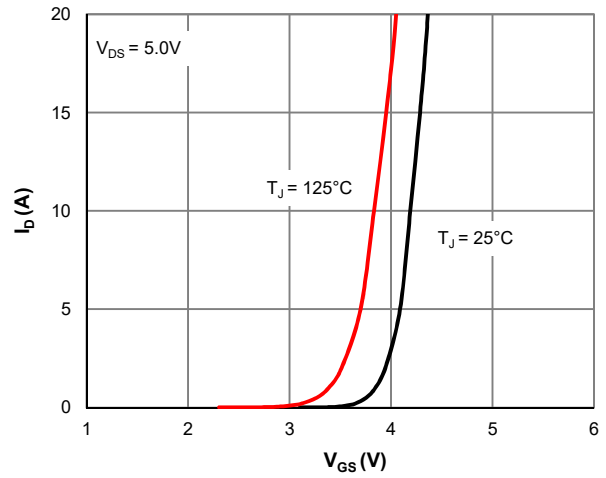
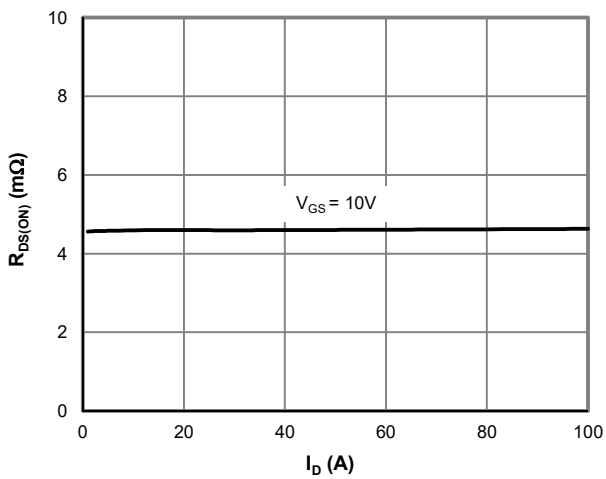
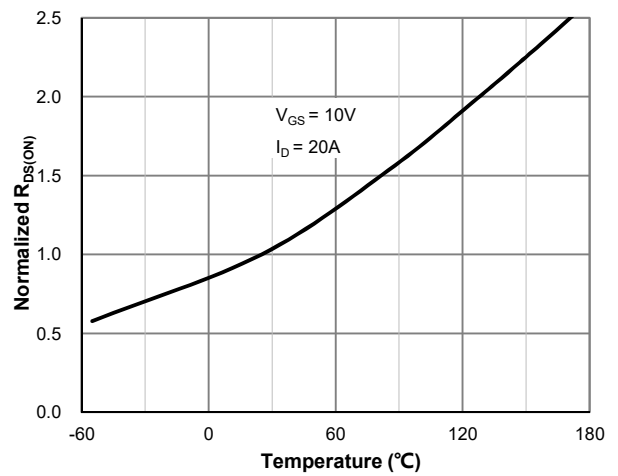
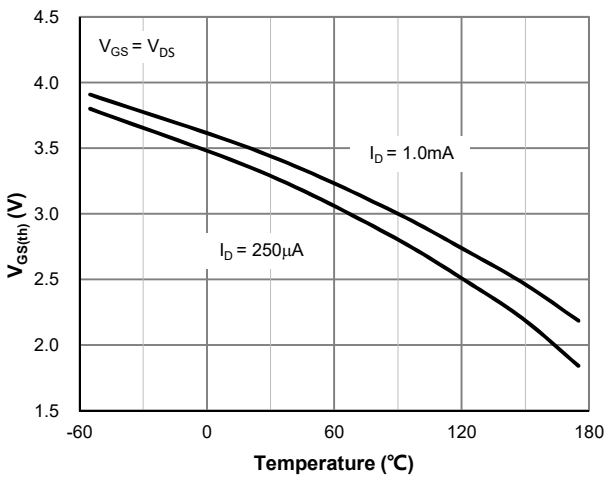
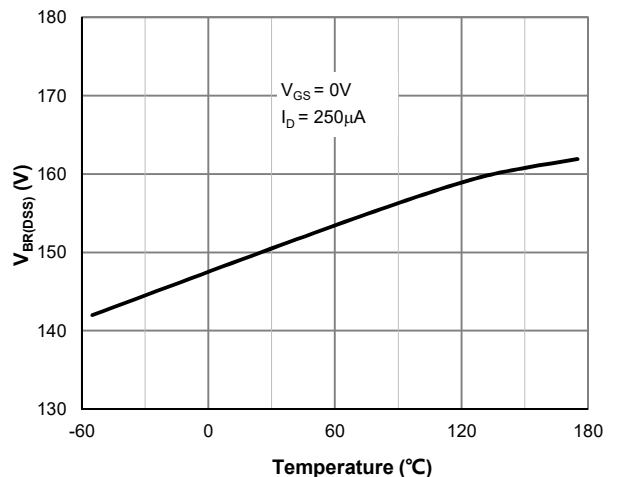
Total Gate Charge (@ $V_{GS} = 10\text{V}$ )	$Q_g$	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 75\text{V}, I_D = 20\text{A}$		68		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$ )	$Q_g$			43		nC
Gate Source Charge	$Q_{gs}$			15.0		nC
Gate Drain Charge	$Q_{gd}$			14.0		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 75\text{V}$ $R_L = 3.75\Omega, R_{GEN} = 6\Omega$		18.5		ns
Turn-On Rise Time	$t_r$			30		ns
Turn-Off DelayTime	$t_{D(off)}$			53		ns
Turn-Off Fall Time	$t_f$			41		ns
Body Diode Reverse Recovery Time	$t_{rr}$		$I_F = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		100	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 20\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		150		nC

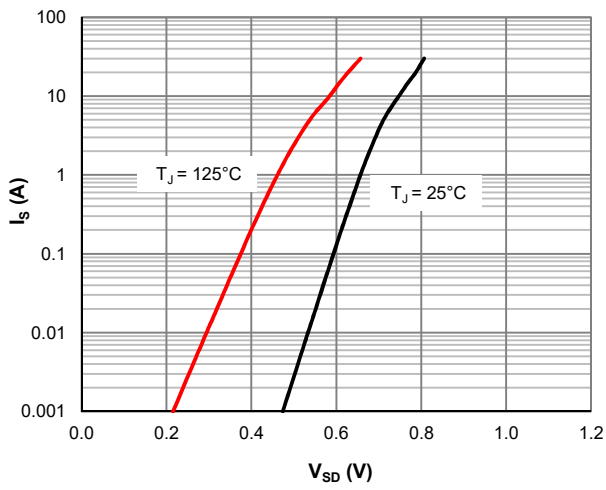
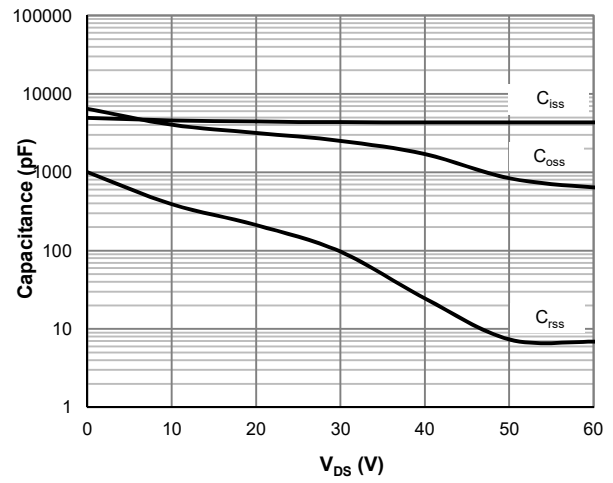
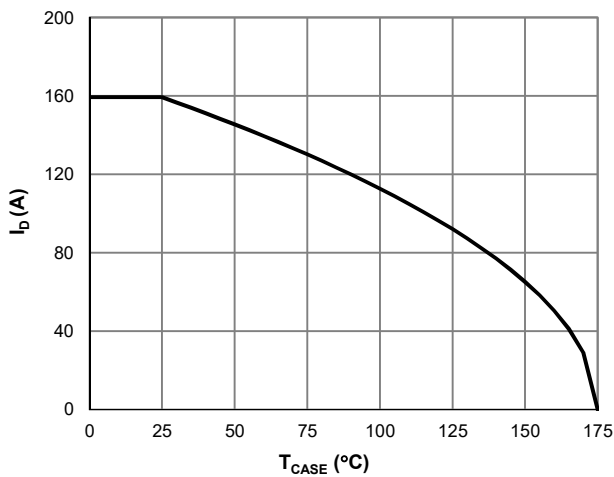
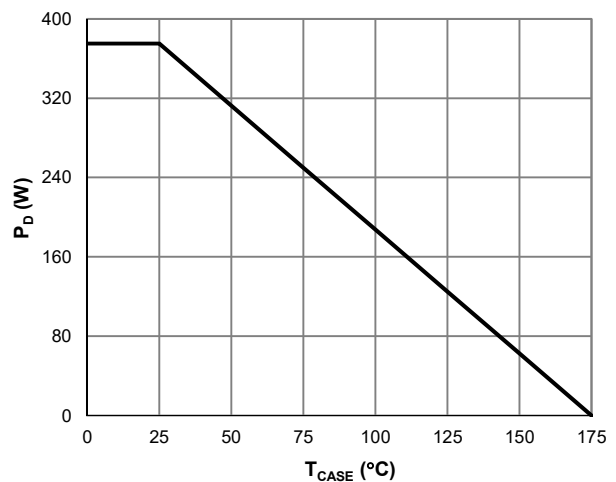
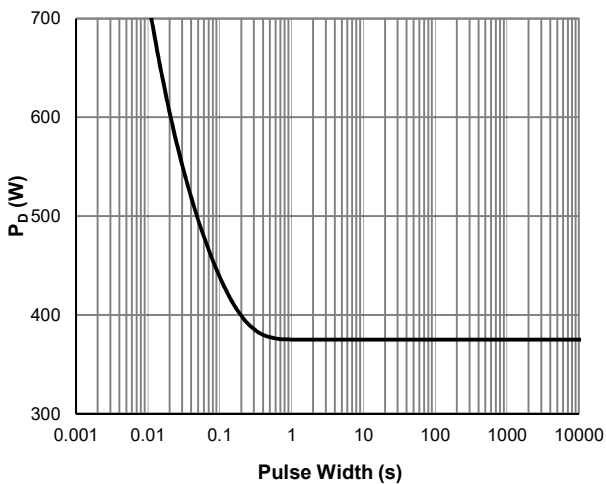
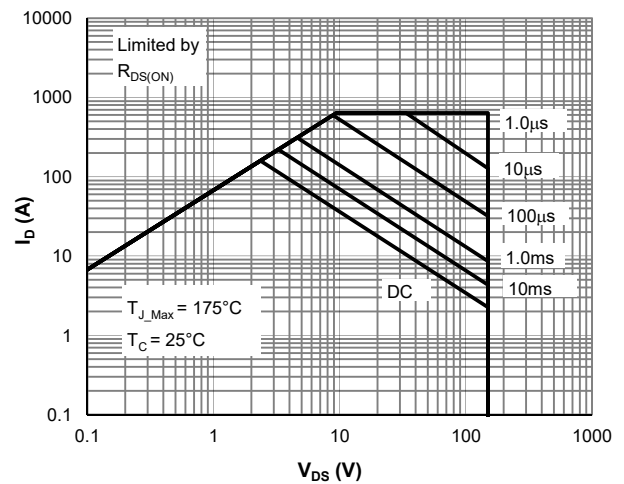
**Thermal Performance**

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	45	55	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.40	0.50	$^\circ\text{C}/\text{W}$

**Notes:**

2. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
3. This single-pulse measurement was taken under  $T_{J\_Max} = 175^\circ\text{C}$ .
4. This single-pulse measurement was taken under the following condition [ $L = 1\text{mH}, V_{GS} = 10\text{V}, V_{DD} = 75\text{V}$ ] while its value is limited by  $T_{J\_Max} = 175^\circ\text{C}$ .
5. The power dissipation  $P_D$  is based on  $T_{J\_Max} = 175^\circ\text{C}$ .
6. This value is guaranteed by design hence it is not included in the production test.

**Typical Electrical & Thermal Characteristics**

**Figure 1: Saturation Characteristics**

**Figure 2: Transfer Characteristics**

**Figure 3:  $R_{DS(ON)}$  vs. Drain Current**

**Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature**

**Figure 5:  $V_{GS(th)}$  vs. Junction Temperature**

**Figure 6:  $V_{BR(DSS)}$  vs. Junction Temperature**

**Typical Electrical & Thermal Characteristics**

**Figure 7: Body-Diode Characteristics**

**Figure 8: Capacitance Characteristics**

**Figure 9: Current De-rating**

**Figure 10: Power De-rating**

**Figure 11: Single Pulse Power Rating, Junction-to-Case**

**Figure 12: Maximum Safe Operating Area**



### Typical Electrical & Thermal Characteristics

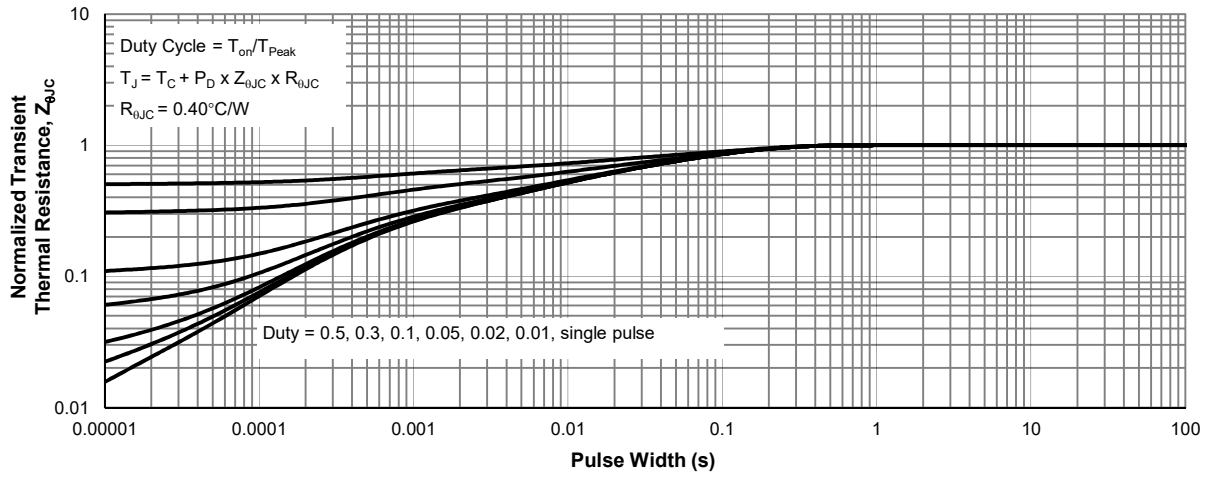


Figure 13: Normalized Maximum Transient Thermal Impedance

